

Datenblatt 24C65 Microchip:

- **Endurance:**
 - 10,000,000 E/W cycles for a High Endurance Block
 - 1,000,000 E/W cycles for a Standard Endurance Block
- **Electrostatic Discharge Protection > 4000V**
- **Data Retention > 200 years**

Definition „Data Retention“ aus Datenblatt von ST Microelectronics

3 Data retention

This section intends to offer all details concerning the data retention capabilities of the ST25DVxxx products based on CMOS F8H process, industrial ranges 6 and 8.

Data retention definition:

- *At t_0 , bytes are written, and then no Write is executed on these bytes. The data retention time is the time, after t_0 , during which the bytes can still be correctly read (the EEPROM devices being DC supplied or not).*